

Vishay Semiconductors

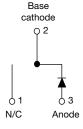
# Ultralow V<sub>F</sub> Hyperfast Rectifier for Discontinuous Mode PFC, 8 A FRED Pt<sup>®</sup>

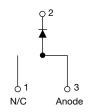




TO-263AB (D<sup>2</sup>PAK)

TO-262AA





VS-8ETL06SPbF

VS-8ETL06-1PbF

PRODUCT SUMMARY	7
Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA
I <sub>F(AV)</sub>	8 A
V <sub>R</sub>	600 V
V <sub>F</sub> at I <sub>F</sub>	0.81 V
t <sub>rr</sub> typ.	60 ns
T <sub>J</sub> max.	175 °C
Diode variation	Single die

#### **FEATURES**

• Benchmark ultralow forward voltage drop



- Hyperfast recovery time
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

ROHS COMPLIANT HALOGEN FREE

- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION**

State of the art, ultralow  $V_F$ , soft-switching hyperfast rectifiers optimized for discontinuous (critical) mode (DCM) power factor correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

#### **APPLICATIONS**

AC/DC SMPS 70 W to 400 W

e.g. laptop and printer AC adaptors, desktop PC, TV and monitor, games units and DVD AC/DC power supplies.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V			
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 160 °C	8				
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	175	А			
Peak repetitive forward current	I <sub>FM</sub>		16				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A	-	0.96	1.05	V	
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	0.81	0.86		
Б		$V_R = V_R$ rated	-	0.05	5		
Reverse leakage current I <sub>R</sub>		T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	20	100	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	17	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ	



# VS-8ETL06SPbF, VS-8ETL06-1PbF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 1$	00 A/μs, V <sub>R</sub> = 30 V	1	60	100	
Boyerea reasyery time		$I_F = 8 \text{ A}, dI_F/dt = 1$	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		150	250	no
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	170	-	ns
		T <sub>J</sub> = 125 °C		-	250	-	
Dook room ourrent	,	T <sub>J</sub> = 25 °C		-	15	-	Α
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	20	-	A
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	1.3	-	
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2.6	-	μC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	1.4	2	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	
Woight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking dayion		Case style TO-263AB (D2PAK)		8ETL06S		
Marking device		Case style TO-262		8ETL06-1		



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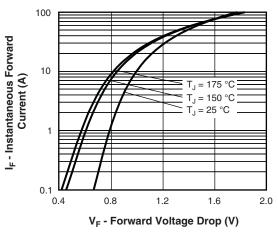


Fig. 1 - Typical Forward Voltage Drop Characteristics

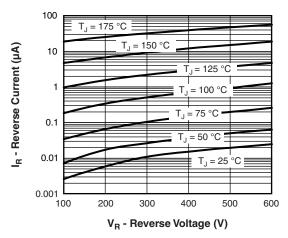


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

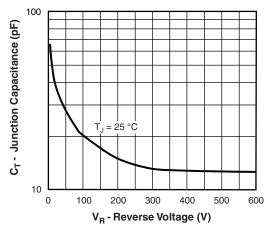


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

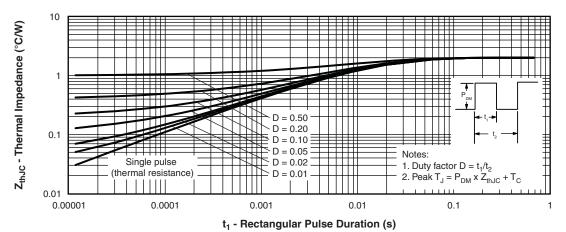


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics





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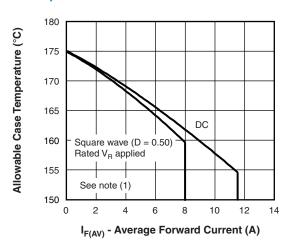


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

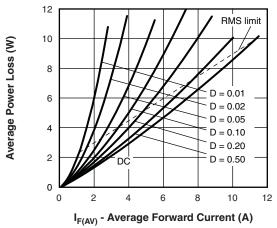


Fig. 6 - Forward Power Loss Characteristics

## Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

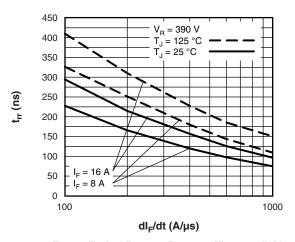


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

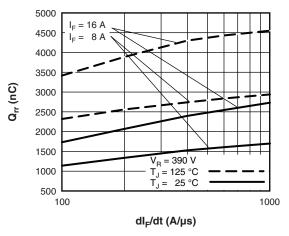


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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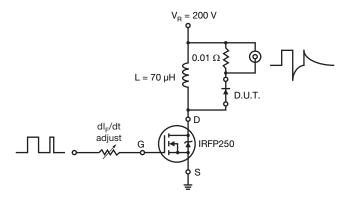
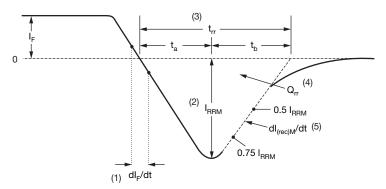


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $\boldsymbol{I}_{\text{RRM}}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

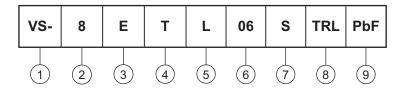
Fig. 10 - Reverse Recovery Waveform and Definitions



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## **ORDERING INFORMATION TABLE**





1 - Vishay Semiconductors product

2 - Current rating (8 A)

- E = single diode

4 - T = TO-220,  $D^2PAK$ 

5 - L = ultralow V<sub>F</sub> hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - • S = D<sup>2</sup>PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D2PAK package)

• TRR = tape and reel (right oriented, for D<sup>2</sup>PAK package)

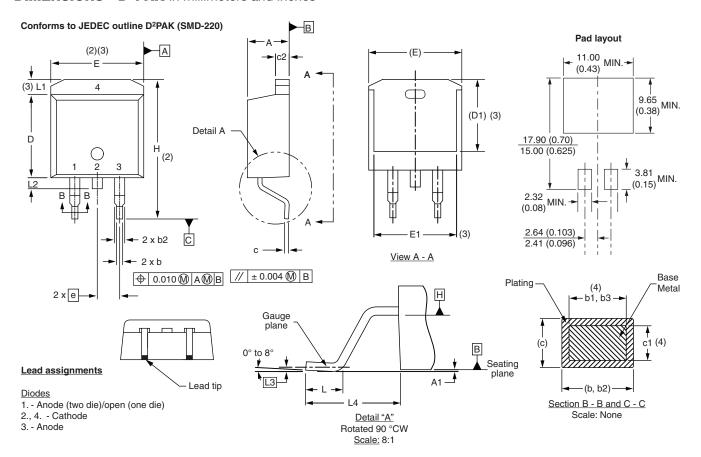
9 - PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95014						
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					
SPICE model	www.vishay.com/doc?96055					

## Vishay Semiconductors

## **D**<sup>2</sup>**PAK**, **TO**-262

## **DIMENSIONS - D<sup>2</sup>PAK** in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIN	IETERS	INCHES		NOTES	
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25 BSC		0.010	BSC		
L4	4.78	5.28	0.188	0.208		

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$  Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

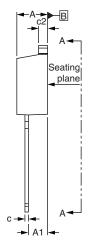
(7) Outline conforms to JEDEC outline TO-263AB

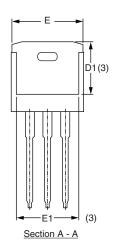
Document Number: 95014 Revision: 31-Mar-09



## **DIMENSIONS - TO-262** in millimeters and inches

# 





**⊕** 0.010 **M** A **M** B

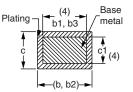
#### Lead assignments



**-**-3 x b2 --3 x b

<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIMETERS		INC	INCHES		
	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100	) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

### Notes

- $^{(1)}$  Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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